

isc N-Channel MOSFET Transistor

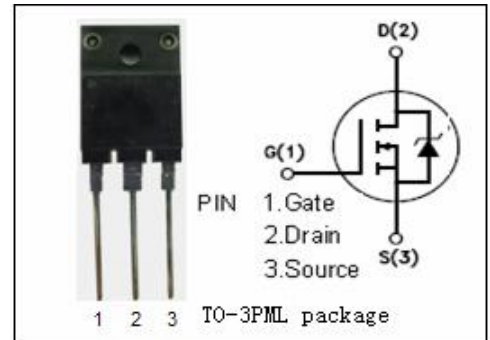
2SK1212

DESCRIPTION

- Drain Current $-I_D=5A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}=900V(\text{Min})$
- Fast Switching Speed

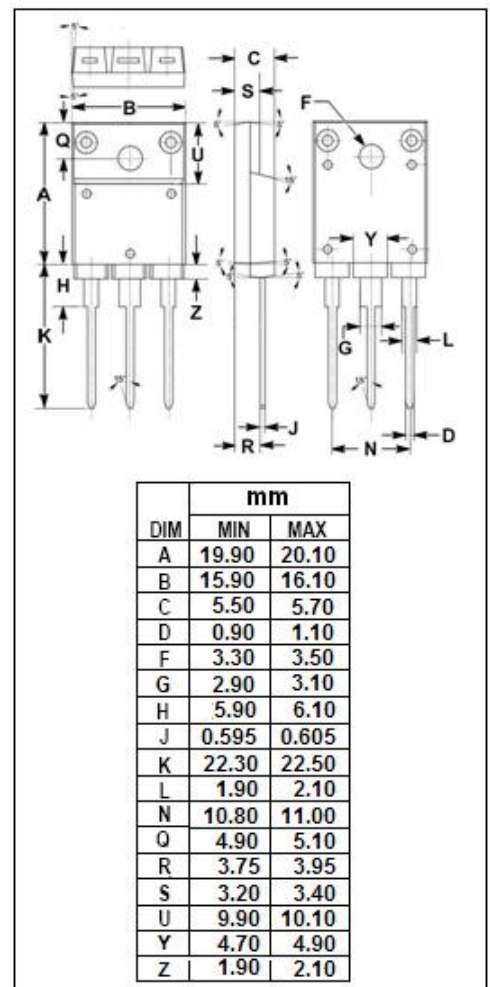
APPLICATIONS

- high voltage, high speed power switching



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	900	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C=25^\circ C$	5	A
P_{tot}	Total Dissipation@ $T_C=25^\circ C$	80	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	1.56	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance,Junction to Ambient	30	$^\circ C/W$

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• ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=1\text{mA}$	900			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=1\text{mA}$	2.1	3.0	4.0	V
$R_{DS(on)}$	Drain-Source On-stage Resistance	$V_{GS}=10\text{V}; I_D=2.5\text{A}$		2.0	2.5	Ω
I_{GSS}	Gate Source Leakage Current	$V_{GS}= \pm 20\text{V}; V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=900\text{V}; V_{GS}=0$			500	μA
V_{SD}	Forward On-Voltage	$I_S=5\text{A}; V_{GS}=0$		1.0	1.5	V
t_r	Rise time	$V_{GS}=10\text{V}; I_D=2.4\text{A};$ $R_L=50\ \Omega$		80	120	ns
t_{on}	Turn-on time			110	170	ns
t_f	Fall time			120	180	ns
t_{off}	Turn-off time			420	630	ns